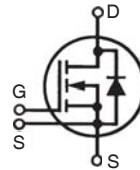


**Linear™ Power MOSFET**  
**w/ Extended FBSOA**

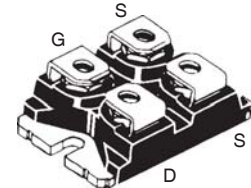
**IXTN17N120L**

N-Channel Enhancement Mode  
Avalanche Rated  
Guaranteed FBSOA



$V_{DSS} = 1200V$   
 $I_{D25} = 15A$   
 $R_{DS(on)} \leq 900m\Omega$

miniBLOC  
E153432



G = Gate      D = Drain  
S = Source

Either Source Terminal S can be used as the Source Terminal or the Kelvin Source (Gate Return) Terminal.

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	1200	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	1200	V
$V_{GSS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ C$	15	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	34	A
$I_A$	$T_C = 25^\circ C$	8.5	A
$E_{AS}$	$T_C = 25^\circ C$	2.5	J
$P_D$	$T_C = 25^\circ C$	540	W
$T_J$		-55 to +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 to +150	$^\circ C$
$V_{ISOL}$	50/60 Hz, RMS, $t = 1$ minute	2500	V~
	$I_{ISOL} \leq 1mA$ , $t = 1s$	3000	V~
$M_d$	Mounting Torque for Base Plate	1.5/13	Nm/lb.in.
	Terminal Connection Torque	1.3/11.5	Nm/lb.in.
<b>Weight</b>		30	g

**Features**

- Designed for Linear Operations
- International Standard Package
- Molding Epoxies Meet UL94 V-0 Flammability Classification
- Guaranteed FBSOA at  $60^\circ C$
- miniBLOC with Aluminum Nitride Isolation
- Low  $R_{DS(on)}$  HDMOS™ Process
- Rugged Polysilicon Gate Cell Structure
- Low Package Inductance

**Advantages**

- Easy to Mount
- Space Savings
- High Power Density

**Applications**

- Programmable Loads
- Current Regulators
- DC-DC Convertors
- Battery Chargers
- DC Choppers
- Temperature and Lighting Controls

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 1mA$	1200		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	3.0		6.0 V
$I_{GSS}$	$V_{GS} = \pm 30V$ , $V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ $T_J = 125^\circ C$			50 $\mu A$ 2 mA
$R_{DS(on)}$	$V_{GS} = 20V$ , $I_D = 8.5A$ , Note 1			900 m $\Omega$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values			
		Min.	Typ.	Max.	
$g_{fs}$	$V_{DS} = 20\text{V}$ , $I_D = 8.5\text{A}$ , Note 1	3.5	5.0	6.5	S
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		8300		pF
$C_{oss}$			520		pF
$C_{rss}$			90		pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 15\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 8.5\text{A}$ $R_G = 2\Omega$ (External)		42		ns
$t_r$			31		ns
$t_{d(off)}$			110		ns
$t_f$			83		ns
$Q_{g(on)}$		$V_{GS} = 15\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 8.5\text{A}$		155	
$Q_{gs}$			41		nC
$Q_{gd}$			60		nC
$R_{thJC}$				0.23	$^\circ\text{C/W}$
$R_{thCS}$		0.05			$^\circ\text{C/W}$

### Safe Operating Area Specification

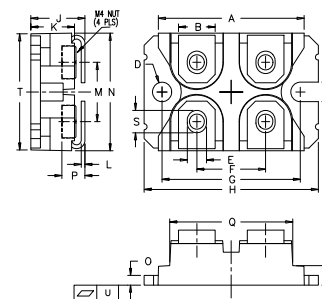
Symbol	Test Conditions	Characteristic Values			
		Min.	Typ.	Max.	
<b>SOA</b>	$V_{DS} = 800\text{V}$ , $I_D = 0.23\text{A}$ , $T_C = 60^\circ\text{C}$ , $t_p = 3\text{s}$	184			W

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values			
		Min.	Typ.	Max.	
$I_S$	$V_{GS} = 0\text{V}$			17	A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			50	A
$V_{SD}$	$I_F = 17\text{A}$ , $V_{GS} = 0\text{V}$ , Note 1			1.5	V
$t_{rr}$	$I_F = I_S$ , $-di/dt = 100\text{A}/\mu\text{s}$ , $V_R = 100\text{V}$		1830		ns

Note: 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

### SOT-227B (IXTN) Outline



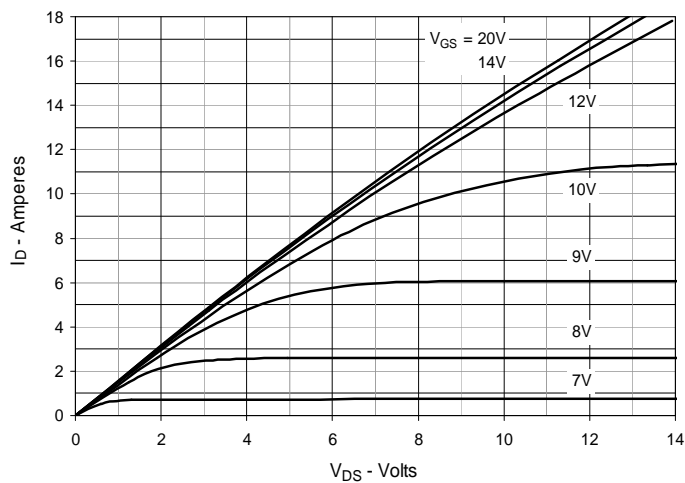
(M4 screws (4x) supplied)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

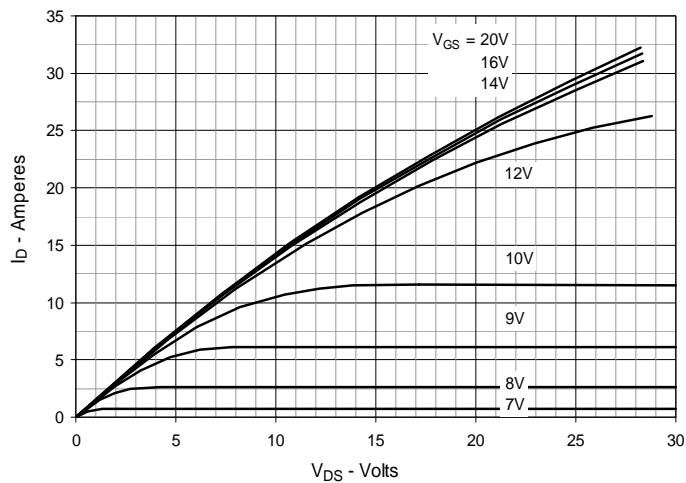
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

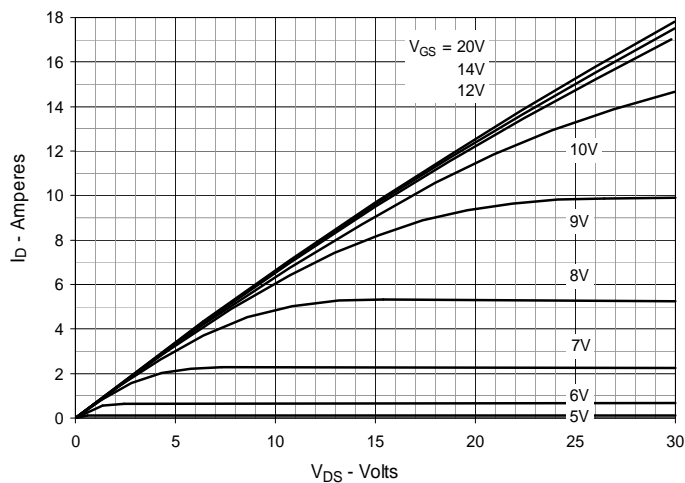
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



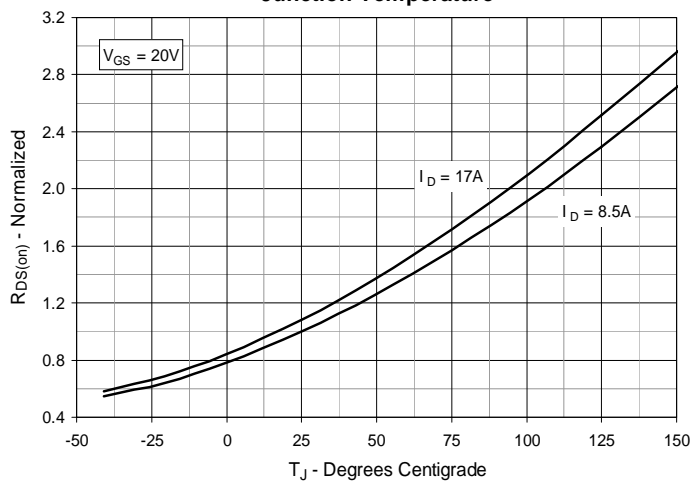
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



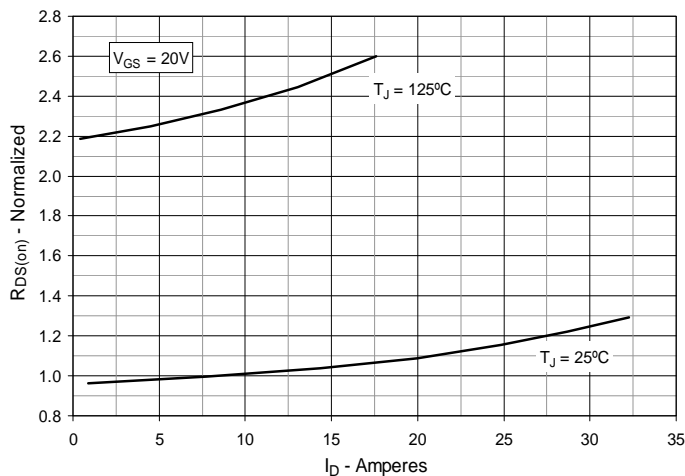
**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$**



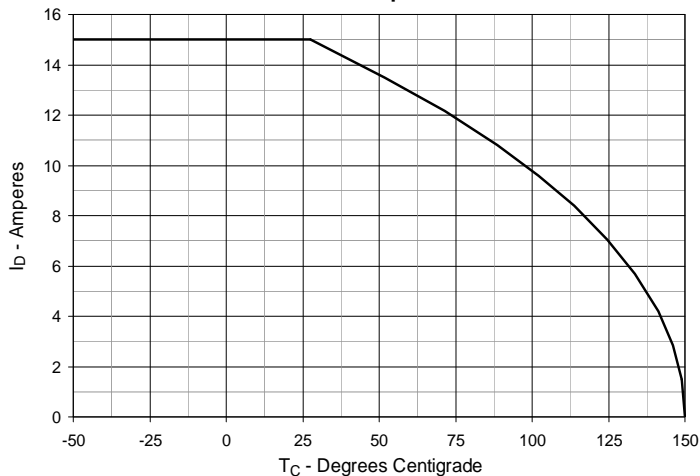
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 8.5\text{A}$  Value vs. Junction Temperature**



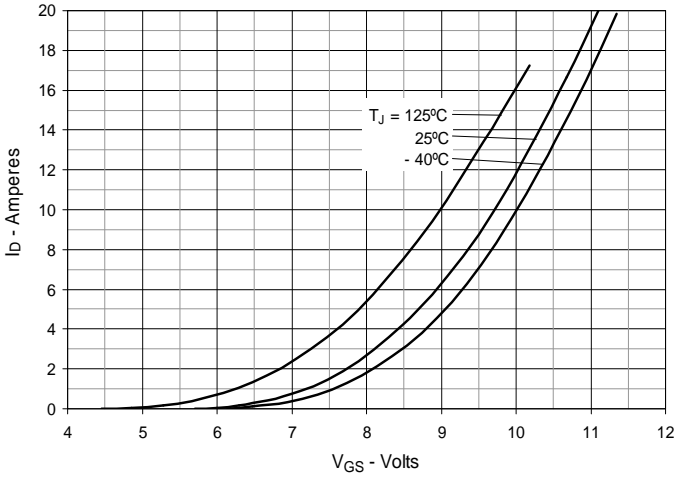
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 8.5\text{A}$  Value vs. Drain Current**



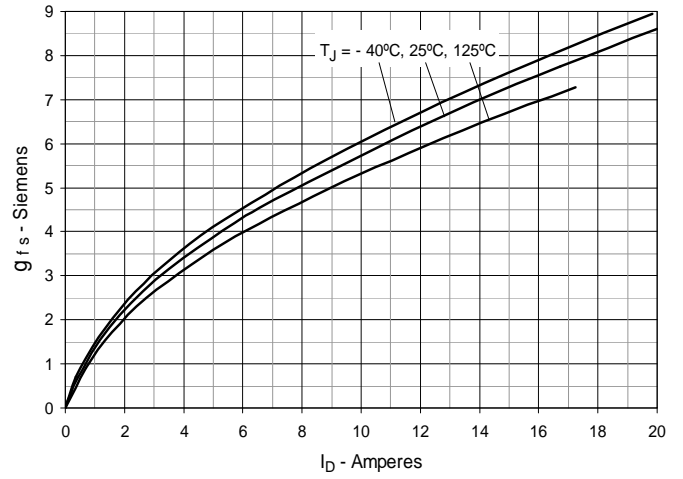
**Fig. 6. Maximum Drain Current vs. Case Temperature**



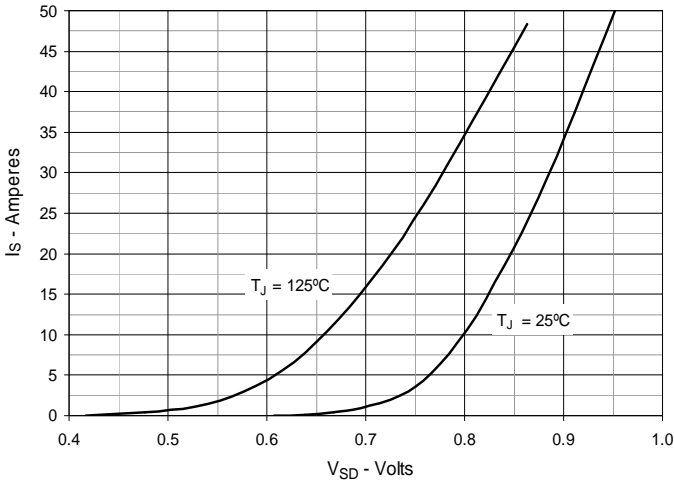
**Fig. 7. Input Admittance**



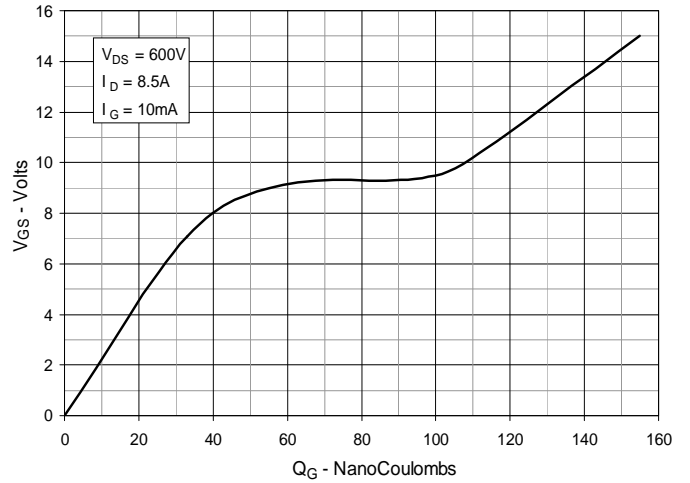
**Fig. 8. Transconductance**



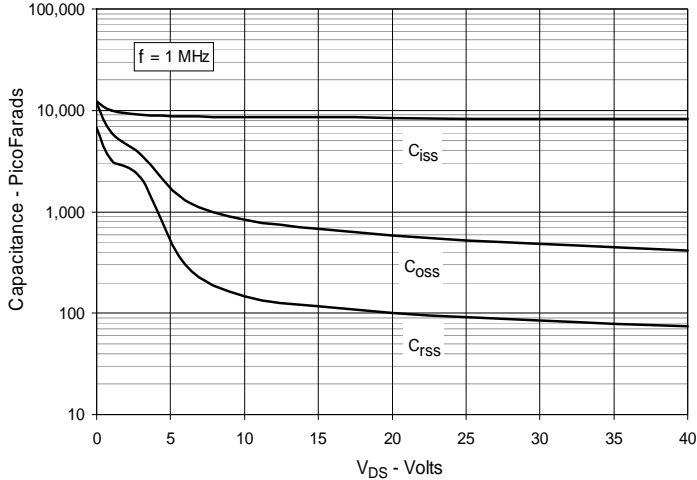
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



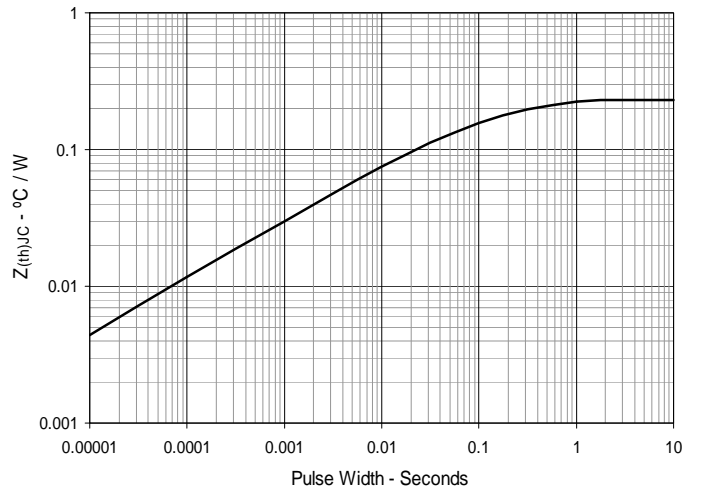
**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**

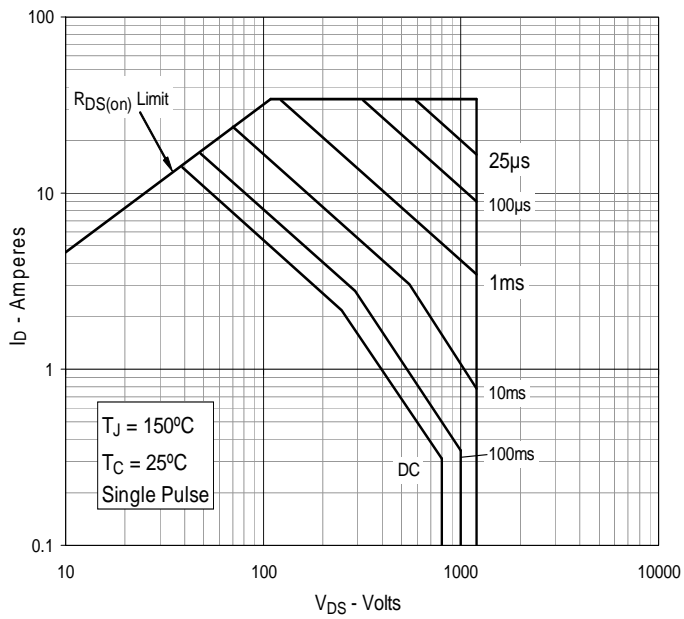


**Fig. 12. Maximum Transient Thermal Impedance**



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**Fig. 13. Forward-Bias Safe Operating Area**  
@  $T_C = 25^\circ\text{C}$



**Fig. 14. Forward-Bias Safe Operating Area**  
@  $T_C = 60^\circ\text{C}$

